

High speed switching series 5<sup>th</sup> generation

**Maximum Ratings**

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	$V_{CE}$	650	V
DC collector current, limited by $T_{vjmax}$ $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$	$I_C$	62.0 39.5	A
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpuls}$	120.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}$	-	120.0	A
Diode forward current, limited by $T_{vjmax}$ $T_c = 25^{\circ}\text{C}$ value limited by bondwire $T_c = 100^{\circ}\text{C}$	$I_F$	40.0 39.5	A
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpuls}$	120.0	A
Gate-emitter voltage Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )	$V_{GE}$	$\pm 20$ $\pm 30$	V
Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$	$P_{tot}$	188.0 94.0	W
Operating junction temperature	$T_{vj}$	-40...+175	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^{\circ}\text{C}$
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020)		260	$^{\circ}\text{C}$

**Thermal Resistance**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b><math>R_{th}</math> Characteristics</b>						
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.80	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		-	-	1.00	K/W
Thermal resistance, min. footprint junction - ambient	$R_{th(j-a)}$		-	-	65	K/W
Thermal resistance, 6cm <sup>2</sup> Cu on PCB junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

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**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.20\text{mA}$	650	-	-	V
Collector-emitter saturation voltage	$V_{CESat}$	$V_{GE} = 15.0\text{V}, I_C = 30.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.35	1.70	V
			-	1.50	-	
			-	1.60	-	
Diode forward voltage	$V_F$	$V_{GE} = 0\text{V}, I_F = 30.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.45	1.70	V
			-	1.42	-	
			-	1.39	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.30\text{mA}, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
			-	1400	-	
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE} = 20\text{V}, I_C = 30.0\text{A}$	-	42.0	-	S

**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	1800	-	pF
Output capacitance	$C_{oes}$		-	55	-	
Reverse transfer capacitance	$C_{res}$		-	7	-	
Gate charge	$Q_G$	$V_{CC} = 520\text{V}, I_C = 30.0\text{A},$ $V_{GE} = 15\text{V}$	-	70.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	7.0	-	nH

**Switching Characteristic, Inductive Load**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

**IGBT Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$**

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 30.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 13.0\Omega, R_{G(off)} = 13.0\Omega,$ $L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ $L_{\sigma}, C_{\sigma}$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	17	-	ns
Rise time	$t_r$		-	12	-	ns
Turn-off delay time	$t_{d(off)}$		-	124	-	ns
Fall time	$t_f$		-	30	-	ns
Turn-on energy	$E_{on}$		-	0.56	-	mJ
Turn-off energy	$E_{off}$		-	0.32	-	mJ
Total switching energy	$E_{ts}$	-	0.88	-	mJ	